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Progress In Digital Integrated Electronics

Complexity of integrated circuits has approximately doubled every year since their introduction. Cost per function has decreased several thousand-fold, while system performance and reliability have been improved dramatically. Many aspects of processing and design technology have contributed to make the manufacture of such functions as complex single chip microprocessors or memory circuits economically feasible. It is possible to analyze the increase in complexity plotted in Figure 1 into different factors that can, in turn, be examined to see what contributions have been important in this development and how they might be expected to continue to evolve. The expected trends can be recombined to see how long exponential growth in complexity can be expected to continue.

A first factor is the area of the integrated structures. Chip areas for some of the largest of the circuits used in constructing Figure 1 are plotted in Figure 2. Here again, the trend follows an exponential quite well, but with significantly lower slope than the complexity curve. Chip area tor maximum complexity has increased by a factor of approximately 20 from the first planar transistor in 1959 to the 16,384-bit charge-coupled device memory chip that corresponds to the point plotted for 1975, while complexity, according to the annual doubling law, should have increased about 65,000-fold. Clearly much of the increased complexity had to result from higher density of components on the chip, rather than from the increased area available through the use of larger chips.

Figure 1 Approximate component count for complex integrated circuits vs. year of Introduction.

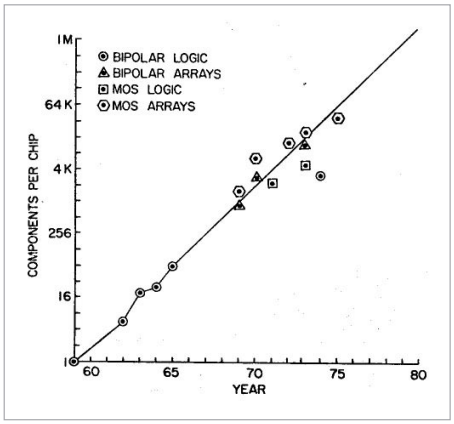
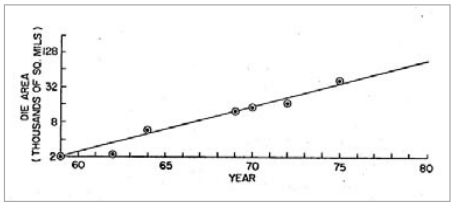


Figure 2 Increase in die area for most complex integrated devices commercially available.



Density was increased partially by using finer scale microstructures. The first integrated circuits of 1961 used line widths of 1 mil (~25 micrometers) while the 1975 device uses 5 micrometer lines. Both line width and spacing between lines are equally important in improving density. Since they have not always been equal,

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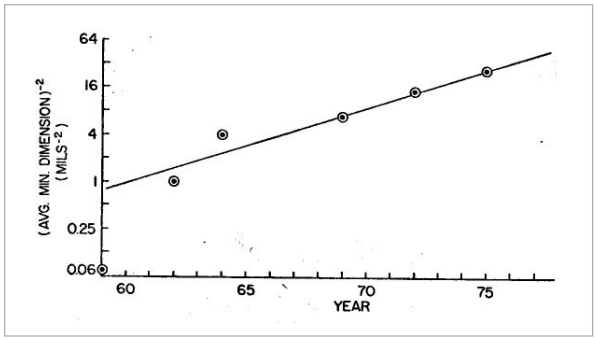
Figure 3 Device density contribution from the decrease in line widths and spacings.

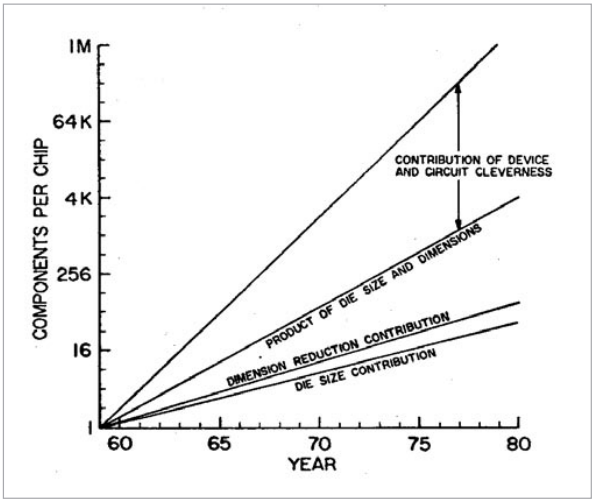


the average of the two is a good parameter to relate to the area that a structure might occupy. Density can be expected to be proportional to the reciprocal of area, so the contribution to improve density vs. time from the use of smaller dimensions is plotted in Figure 3.

Neglecting the first planar transistor, where very conservative line width and spacing was employed, there is again a reasonable fit to an exponential growth. From the exponential approximation represented by the straight line in Figure 3, the increase in density from this source over the 1959-1975 period is a factor of approximately 32.

Combining the contribution of larger chip area and higher density resulting from geometry accounts for a 640-fold increase in complexity, leaving a factor of about 100 to account for through 1975, as is shown graphically in Figure 4. This factor is the contribution of circuit and device advances to higher density. It is noteworthy that this contribution to complexity has been more important than either increased chip area or finer lines. Increasingly the surface areas of the integrated devices have been committed to components rather than to such inactive structures as device isolation and interconnections, and the components themselves have trended toward minimum size, consistent with the dimensional tolerances employed.

Figure 4 Decomposition of the complexity curve into various components.



Can these trends continue?

Extrapolating the curve for die size to 1980 suggests that chip area might be about 90,000 sq. mils, or the equivalent of 0.3 inches square. Such a die size is clearly consistent with the 3 inch wafer presently widely used by the industry. In fact, the size of the wafers themselves have grown about as fast as has die size during the time period under consideration and can be expected to continue to grow. Extension to larger die size depends principally upon the continued reduction in the density of defects. Since the existence of the type of defects that harm integrated circuits is not fundamental, their density can be reduced as long as such reduction has sufficient economic merit to justify the effort. I see sufficient continued merit to expect progress to continue for the next several years. Accordingly, there is no present reason to expect a change in the trend shown in Figure 2.

With respect to dimensions, in these complex devices we are still far from the minimum device sizes limited by such fundamental considerations as the charge on the electron or the atomic structure of matter. Discrete devices with sub-micrometer dimensions show that no basic problems should be expected at least until the average line width and

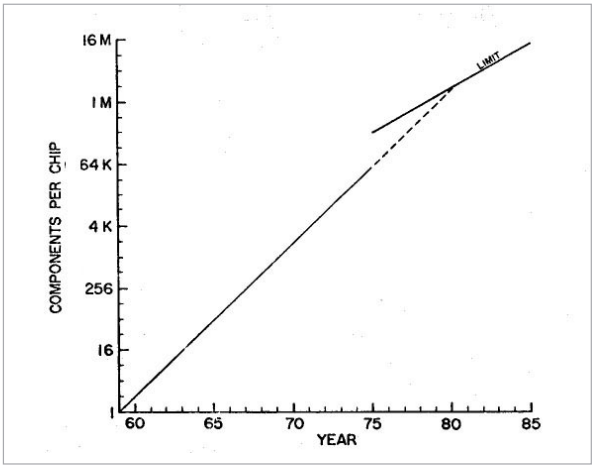
spaces are a micrometer or less. This allows for an additional factor of improvement at least equal to the contribution from the finer geometries of the last fifteen years. Work in non-optical masking techniques, both electron beam and X-ray, suggests that the required resolution capabilities will be available. Much work is required to be sure that defect densities continue to improve as devices are scaled to take advantage of the improved resolution. However, I see no reason to expect the rate of progress in the use of smaller minimum dimensions in complex circuits to decrease in the near future. This contribution should continue along the curve of Figure 3.

With respect to the factor contributed by device and circuit cleverness, however, the situation is different. Here we are approaching a limit that must slow the rate of progress. The CCD structure can approach closely the maximum density practical. This structure requires no contacts to the components within the array, but uses gate electrodes that can be at minimum spacing to transfer charge and information from one location to the next. Some improvement in overall packing efficiency is possible beyond the structure plotted as the 1975 point in Figure 1, but it is unlikely that the packing efficiency alone can contribute as much as a factor of four, and this only in serial data paths. Accordingly, I am Inclined to suggest a limit to the contribution of circuit and device cleverness of another factor of four in component density.

With this factor disappearing as an important contributor, the rate of increase of complexity can be expected to change slope in the next few years as shown in Figure 5. The new slope might approximate a doubling every two years, rather than every year, by the end of the decade.

Even at this reduced slope, integrated structures containing several million components can be expected within ten years. These new devices will continue to reduce the cost of electronic functions and extend the utility of digital electronics more broadly throughout society.

Figure 5 Projection of the complexity curve reflecting the limit on increased density through invention.



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